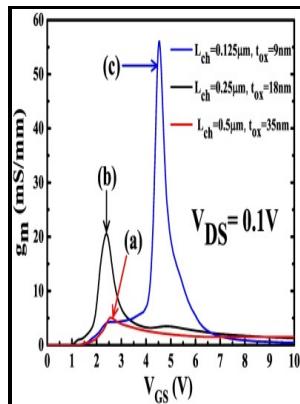


Lateral superjunction power MOSFETs.

National Library of Canada - MDmesh: 20 Years of Superjunction STPOWER™ MOSFETs, A Story About Innovation



Description: -

-Lateral superjunction power MOSFETs.

-Canadian theses = -- Thèses canadiennes Lateral superjunction power MOSFETs.

Notes: Thesis (M.A.Sc.) -- University of Toronto, 2001.

This edition was published in 2001



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Extended Trench Gate Superjunction Lateral Power MOSFET for Ultra

Typical discrete transistors include power MOSFETs and IGBTs Insulated Gate Bipolar Transistors.

Exicon Lateral MOSFETs

Then, as shown in FIG.

Figure 4 from Superjunction Power Devices, History, Development, and Future Prospects

Unlike the conventional SJ structure, a thin oxide layer is formed in between the p-n columns to avoid the p-n column interdiffusion Gan et al. Figure 3 compares the electric field in the drift region vs.

Figure 4 from Superjunction Power Devices, History, Development, and Future Prospects

The mesa width, that is, the space between trenches, may be about 1. Planar MOSFETs typically have a high drain-to-source resistance per unit of silicon area, and come with relatively higher drain source resistances.

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